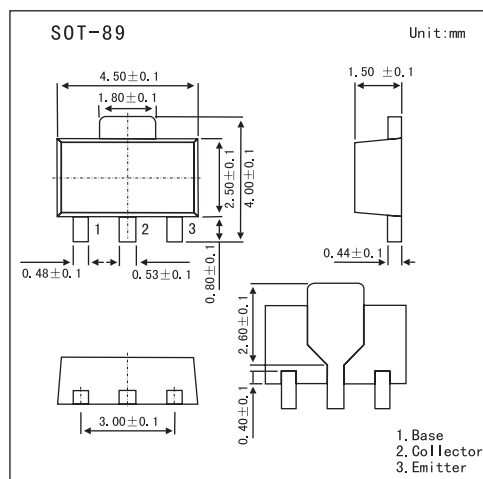


# 2SB1119

### ■ Features

- Very small size making it easy to provide highdensity, small-sized hybrid IC:s.



### ■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V <sub>CB0</sub>	-25	V
Collector-emitter voltage	V <sub>CEO</sub>	-25	V
Emitter-base voltage	V <sub>EBO</sub>	-5	V
Collector current	I <sub>C</sub>	-1	A
Collector current (pulse)	I <sub>CP</sub>	-2	A
Collector dissipation	P <sub>C</sub>	500	mW
Jumction temperature	T <sub>j</sub>	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

### ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I <sub>CBO</sub>	V <sub>CB</sub> = -20V , I <sub>E</sub> = 0			-0.1	μA
Emitter cutoff current	I <sub>EBO</sub>	V <sub>CB</sub> = -4V , I <sub>E</sub> = 0			-0.1	μA
DC current Gain	h <sub>FE</sub>	V <sub>CE</sub> = -2V , I <sub>C</sub> = -50mA	100		560	
		V <sub>CE</sub> = -2V , I <sub>C</sub> = -1A	40			
Gain bandwidth product	f <sub>T</sub>	V <sub>CE</sub> = -10V , I <sub>C</sub> = -50mA		180		MHz
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> = -500mA , I <sub>B</sub> = -50mA		-0.15	-0.7	V
Base-emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> = -500mA , I <sub>B</sub> = -50mA		-0.85	-1.2	V
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> = -10μA , I <sub>E</sub> = 0	-25			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -1mA , R <sub>BE</sub> = ∞	-25			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> = -10μA , I <sub>C</sub> = 0	-5			V
Output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V , f = 1MHz		52		pF

### ■ hFE Classification

Marking	BB			
	R	S	T	U
hFE	100~200	140~280	200~400	280~560